

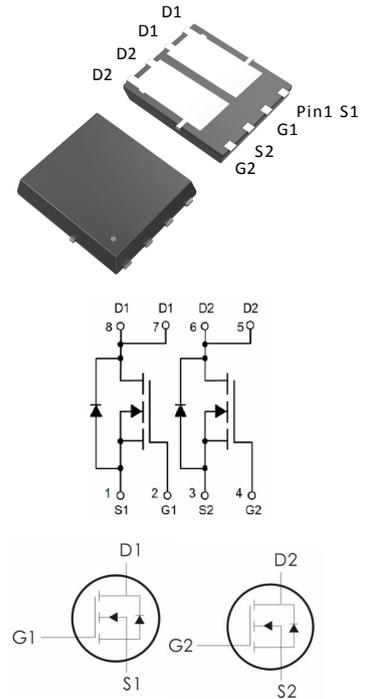
Description:

This Dual N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=60V, I_D=25A, R_{DS(ON)}<25m\Omega @V_{GS}=10V$ (Typ: $18m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
NE030DNG	E030DN	DFN5*6-8D	5000 pcs/Reel

Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current ¹	25	A
	Continuous Drain Current- $T_C=100^\circ C$ ¹	17.5	
I_{DM}	Pulsed Drain Current ²	100	
P_D	Power Dissipation	11	W
E_{AS}	Single pulse avalanche energy ³	17	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	9.5	$^\circ C/W$

Electrical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	60	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=60V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics <small>(Note3)</small>						
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	1	1.67	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance ⁴	$V_{GS}=10V, I_D=10A$	---	18	25	m Ω
		$V_{GS}=4.5V, I_D=5A$	---	25	32.5	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	1030	---	pF
C_{oss}	Output Capacitance		---	68	--	
C_{rss}	Reverse Transfer Capacitance		---	63	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=30V, I_D=20A,$ $R_G=3\ \Omega, V_{GS}=10V$	---	7	---	ns
t_r	Rise Time		---	21	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	16.8	---	ns
t_f	Fall Time		---	24	---	ns
Q_g	Total Gate Charge		$V_{GS}=10V, V_{DS}=30V,$ $I_D=10A$	---	25	---
Q_{gs}	Gate-Source Charge	---		4.5	---	nC
Q_{gd}	Gate-Drain "Miller" Charge	---		6.5	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_{SD}=20A$	---	---	1.2	V
I_S	Continuous Drain Current	$V_D=V_G=0V$	---	---	20.8	A
I_{SM}	Pulsed Drain Current		---	---	83	A
T_{rr}	Reverse Recovery Time	$I_F=10A, T_J=25^\circ\text{C}$	---	29	---	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu\text{s}$	---	49	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : $T_J=25^{\circ}C, V_{DD}=30V, V_G=10V, L=0.1mH$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Test Circuit

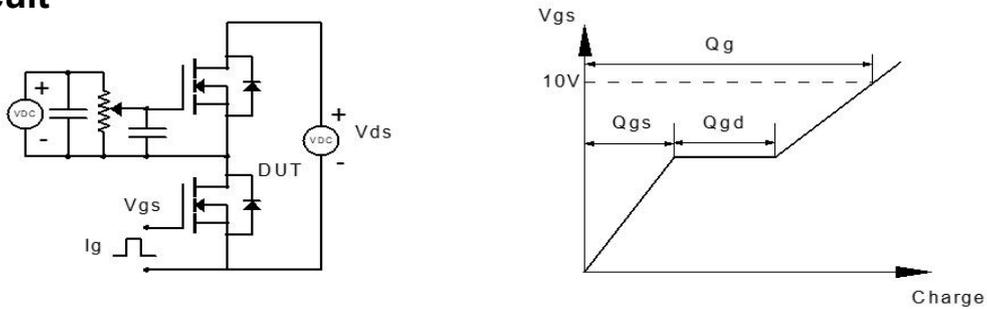


Figure 1: Gate Charge Test Circuit & Waveform

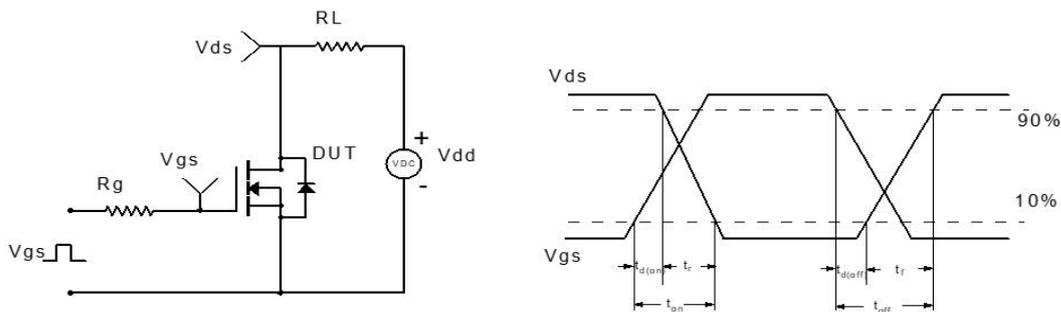


Figure 2: Resistive Switching Test Circuit & Waveform

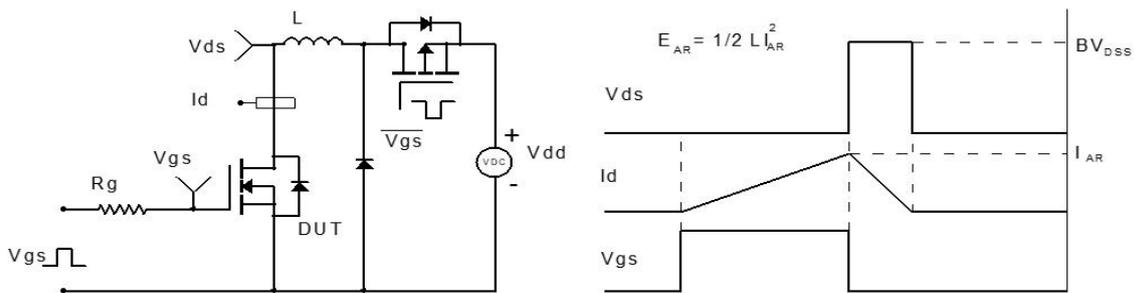


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

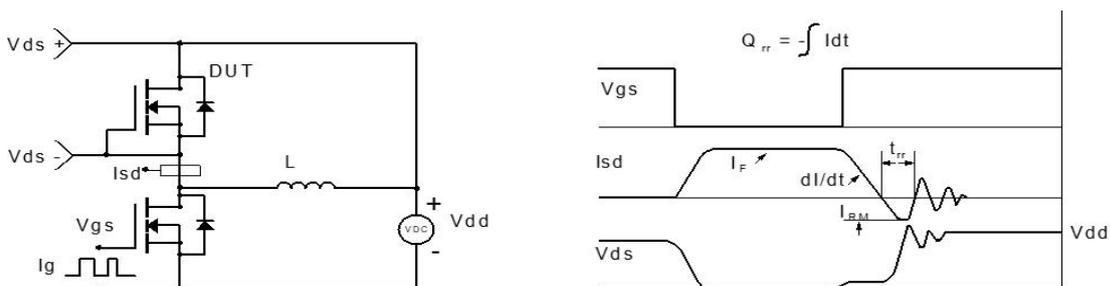
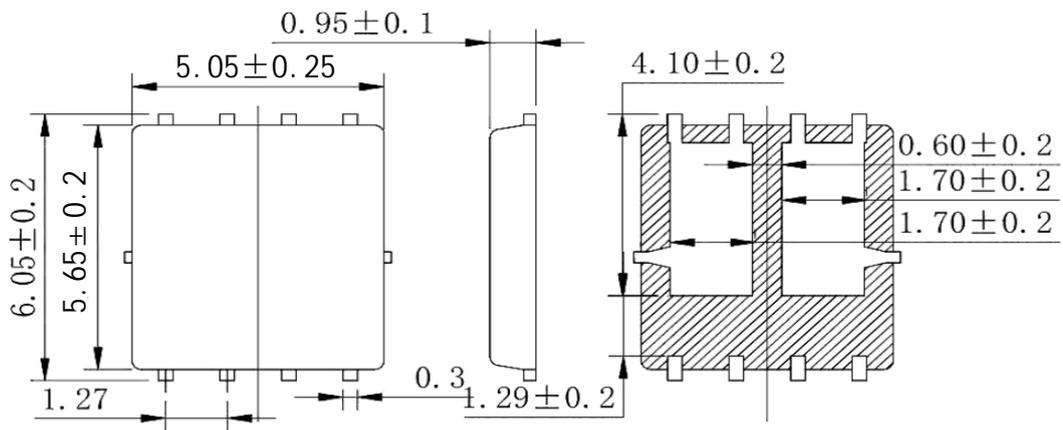
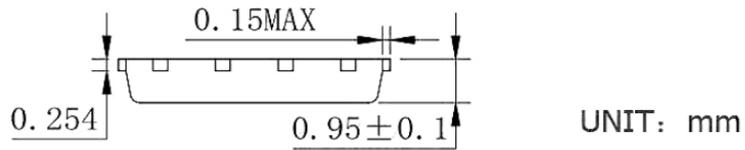


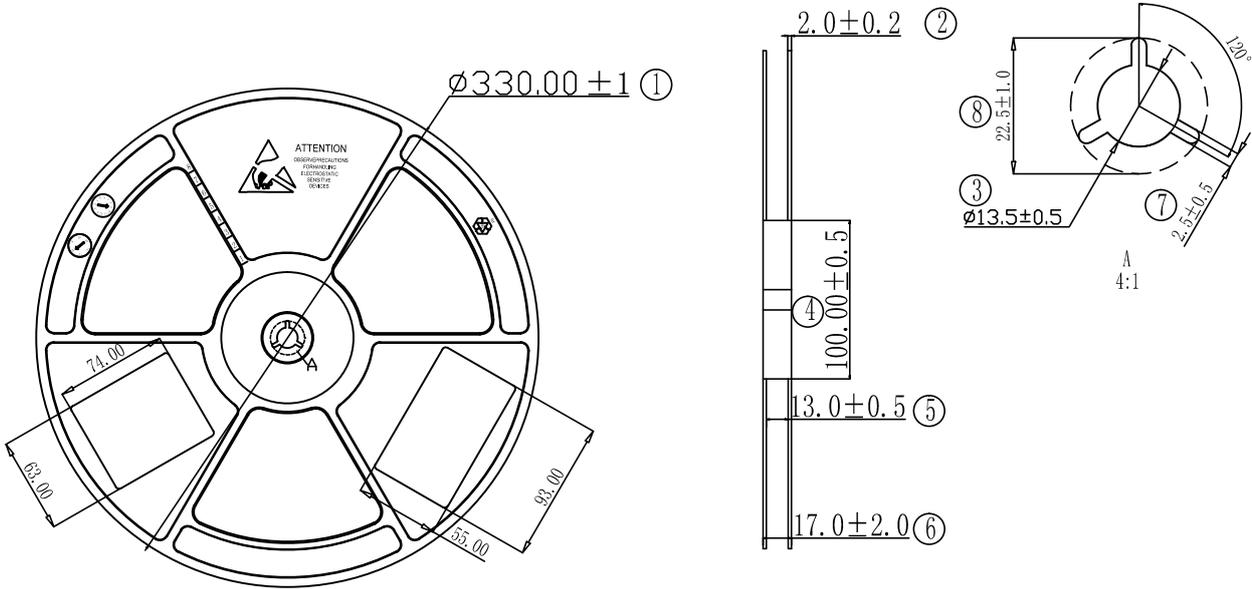
Figure 4: Diode Recovery Test Circuit & Waveform

DFN5x6-8D Package Information:

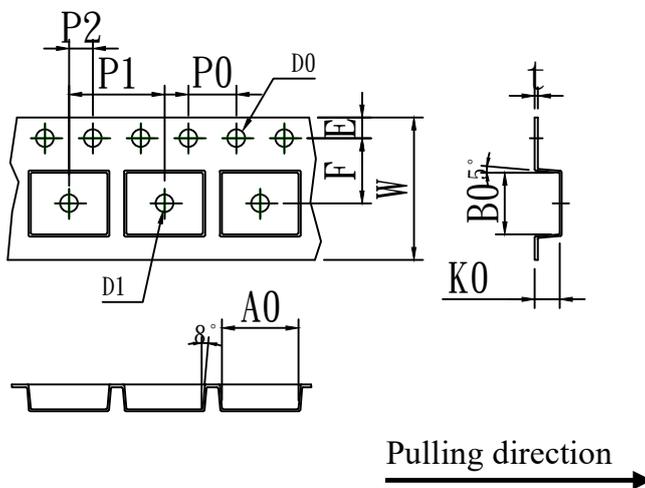


Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	6.15±0.10	5.40±0.10	1.30±0.10	1.55±0.10	1.55±0.10	4.00±0.10	8.00±0.10	40.00±0.10
Symbol	W	E	F	P2	t			
Spec	12.00±0.10	1.75±0.10	5.50±0.10	2.00±0.10	0.20±0.05			



Marking Information:

①. Doingter LOGO

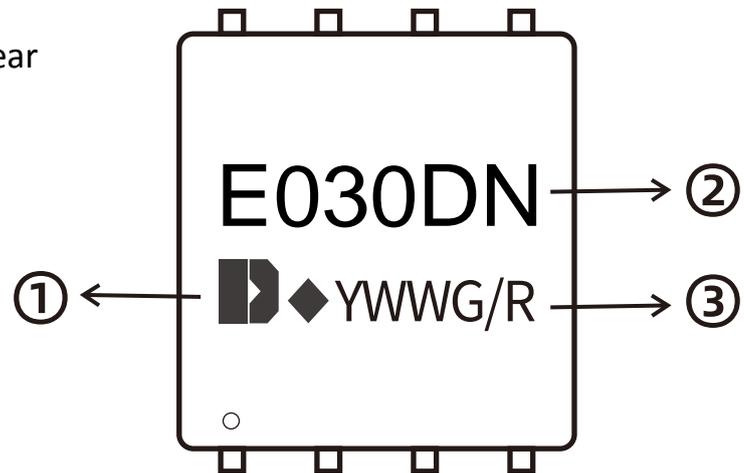
②. Part NO.

③. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)


Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2025-07-22	Release of final version

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